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**Color Code:**

Red – Plasma Etching  
Blue – Advanced Devices

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<http://patft.uspto.gov/netahtml/srchnum.htm>

US Patent Nr.	Title	Assignee	Filed	Date of Patent
6,562,187	Methods and apparatus for determining an etch endpoint in a plasma processing system	Lam Research Corporation	2/23/01	5/13/03
6,562,665	Fabrication of a field effect transistor with a recess in a semiconductor pillar in SOI technology	Advanced Micro Devices, Inc.	10/16/00	5/13/03
6,563,131	Method and structure of a dual/wrap-around gate field effect transistor	International Business Machines Corporation	6/2/00	5/13/03
6,563,152	Technique to obtain high mobility channels in MOS transistors by forming a strain layer on an underside of a channel	Intel Corporation	12/29/00	5/13/03
6,563,183	Gate array with multiple dielectric properties and method for forming same	Advanced Micro Devices, Inc.	2/28/02	5/13/03
6,564,114	Determining endpoint in etching processes using real-time principal components analysis of optical emission spectra	Advanced Micro Devices, Inc.	1/26/00	5/13/03

6,566,177	Silicon-on-insulator vertical array device trench capacitor DRAM	International Business Machines Corporation	10/25/99	5/20/03
6,566,213	Method of fabricating multi-thickness silicide device formed by disposable spacers	Advanced Micro Devices, Inc.	4/2/01	5/20/03
6,566,215	Method of fabricating short channel MOS transistors with source/drain extensions	Chartered Semiconductor Manufacturing Ltd.	6/6/02	5/20/03
6,566,236	Gate structures with increased etch margin for self-aligned contact and the method of forming the same	Integrated Device Technology, Inc.	4/26/00	5/20/03
6,566,270	Integration of silicon etch and chamber cleaning processes	Applied Materials Inc.	9/15/00	5/20/03
6,566,704	Vertical nano-size transistor using carbon nanotubes and manufacturing method thereof	Samsung Electronics Co.	6/27/01	5/20/03
6,567,717	Feed-forward control of TCI doping for improving mass-production-wise, statistical distribution of critical performance parameters in semiconductor devices	Advanced Micro Devices, Inc.	1/19/00	5/20/03
6,569,736	Method for fabricating square polysilicon spacers for a split gate flash memory device by multi-step polysilicon etch	Taiwan Semiconductor Manufacturing Co.	2/14/02	5/27/03
6,569,773	Method for anisotropic plasma-chemical dry etching of silicon nitride layers using a gas mixture containing fluorine	TEMIC Semiconductor GmbH	12/19/99	5/27/03
6,569,774	Method to eliminate striations and surface roughness caused by dry etch	Micron Technology, Inc.	8/31/00	5/27/03

6,569,775	Method for enhancing plasma processing performance	Applied Materials, Inc.	2/17/00	5/27/03
6,569,777	Plasma etching method to form dual damascene with improved via profile	Taiwan Semiconductor Manufacturing Co.	10/2/02	5/27/03
6,570,220	Fabrication of deep submicron structures and quantum wire transistors using hard-mask transistor width definition	Intel Corporation	3/14/00	5/27/03